

Nabiha Ben Sedrine

List of Publications by Year in descending order

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70
papers

1,142
citations

471371

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434063

31
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all docs

70
docs citations

70
times ranked

1706
citing authors

#	ARTICLE	IF	CITATIONS
1	Europium-Implanted AlN Nanowires for Red Light-Emitting Diodes. ACS Applied Nano Materials, 2022, 5, 972-984.	2.4	11
2	Enhancing the luminescence yield of Cr ³⁺ in Ga ² O ₃ by proton irradiation. Applied Physics Letters, 2022, 120, .	1.5	8
3	Luminescent silver nanoclusters decorated on ZnO tetrapods: a detailed understanding of their role in photoluminescence features. Journal of Materials Chemistry C, 2021, 9, 7014-7026.	2.7	9
4	Eu ³⁺ optical activation engineering in Al Ga ¹ -N nanowires for red solid-state nano-emitters. Applied Materials Today, 2021, 22, 100893.	2.3	4
5	Exploring swift-heavy ion irradiation of InGa ⁿ /Ga ⁿ multiple quantum wells for green-emitters: the use of Raman and photoluminescence to assess the irradiation effects on the optical and structural properties. Journal of Materials Chemistry C, 2021, 9, 8809-8818.	2.7	5
6	Clustering and Morphology Evolution of Gold on Nanostructured Surfaces of Silicon Carbide: Implications for Catalysis and Sensing. ACS Applied Nano Materials, 2021, 4, 1282-1293.	2.4	10
7	Silver nanoparticle array on weakly interacting epitaxial graphene substrate as catalyst for hydrogen evolution reaction under neutral conditions. Applied Physics Letters, 2021, 119, 153902.	1.5	2
8	Interplay between thin silver films and epitaxial graphene. Surface and Coatings Technology, 2020, 381, 125200.	2.2	6
9	ZnAl ₂ O ₄ decorated Al-doped ZnO tetrapodal 3D networks: microstructure, Raman and detailed temperature dependent photoluminescence analysis. Nanoscale Advances, 2020, 2, 2114-2126.	2.2	15
10	Photoluminescence investigations of ZnO micro/nanostructures. Materials Today Chemistry, 2020, 16, 100243.	1.7	17
11	Iridium(III)porphyrin arrays with tuneable photophysical properties. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2020, 235, 118309.	2.0	4
12	Modelling of Optical Damage in Nanorippled ZnO Produced by Ion Irradiation. Crystals, 2019, 9, 453.	1.0	4
13	Probing surface states in C ₆₀ decorated ZnO microwires: detailed photoluminescence and cathodoluminescence investigations. Nanoscale Advances, 2019, 1, 1516-1526.	2.2	18
14	Eu Activation in Ga ² -Ga ₂ O ₃ MOVPE Thin Films by Ion Implantation. ECS Journal of Solid State Science and Technology, 2019, 8, Q3097-Q3102.	0.9	15
15	Buckminsterfullerene hybridized zinc oxide tetrapods: defects and charge transfer induced optical and electrical response. Nanoscale, 2018, 10, 10050-10062.	2.8	44
16	Optical investigations of europium ion implanted in nitride-based diode structures. Surface and Coatings Technology, 2018, 355, 40-44.	2.2	9
17	Fluctuating potentials in GaAs:Si nanowires: critical reduction of the influence of polytypism on the electronic structure. Nanoscale, 2018, 10, 3697-3708.	2.8	13
18	Shifting Lu ₂ SiO ₅ crystal to eutectic structure by laser floating zone. Journal of the European Ceramic Society, 2018, 38, 2059-2067.	2.8	13

#	ARTICLE	IF	CITATIONS
37	Defect luminescence in oxides nanocrystals grown by laser assisted techniques. , 2015, , .		2
38	Spectroscopic Analysis of Eu ³⁺ Implanted and Annealed GaN Layers and Nanowires. Journal of Physical Chemistry C, 2015, 119, 17954-17964.	1.5	13
39	Structural, optical, electrical and morphological study of transparent p-NiO/n-ZnO heterojunctions grown by PLD. Proceedings of SPIE, 2015, , .	0.8	4
40	Luminescence studies on SnO ₂ and SnO ₂ :Eu nanocrystals grown by laser assisted flow deposition. Physical Chemistry Chemical Physics, 2015, 17, 13512-13519.	1.3	19
41	Rapid thermal annealing effects on the optical properties of GaAs _{0.9} ^x Sb _{0.1} structures grown by MBE. Materials Science in Semiconductor Processing, 2015, 29, 331-336.	1.9	7
42	Effect of Mg doping on the structural and free-charge carrier properties of InN films. Journal of Applied Physics, 2014, 115, 163504.	1.1	16
43	GaN:Pr ³⁺ nanostructures for red solid state light emission. RSC Advances, 2014, 4, 62869-62877.	1.7	5
44	Infrared to vacuum-ultraviolet ellipsometry and optical Hall-effect study of free-charge carrier parameters in Mg-doped InN. Journal of Applied Physics, 2013, 113, .	1.1	22
45	Bandgap Engineering and Optical Constants of YxAl _{1-x} N Alloys. Japanese Journal of Applied Physics, 2013, 52, 08JM02.	0.8	11
46	Spectroscopic Ellipsometry of AP-MOVPE-Grown GaAs _{1-x} Bi _x Dilute Alloys. Springer Series in Materials Science, 2013, , 167-179.	0.4	0
47	Infrared ellipsometry and near-infrared-to-vacuum-ultraviolet ellipsometry study of free-charge carrier properties in In-polar p-type InN. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	0
48	Temperature dependent effective mass in AlGaIn/GaN high electron mobility transistor structures. Applied Physics Letters, 2012, 101, .	1.5	44
49	Y _x Al _{1-x} N thin films. Journal Physics D: Applied Physics, 2012, 45, 422001.	1.3	42
50	Elaboration and characterization of nanocrystalline TiO ₂ thin films prepared by sol-gel dip-coating. Surface and Coatings Technology, 2011, 206, 243-249.	2.2	53
51	Optical properties of InN/In _{0.73} Ga _{0.27} N multiple quantum wells studied by spectroscopic ellipsometry. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1629-1632.	0.8	1
52	Sol-gel synthesis, characterization and optical properties of mercury-doped TiO ₂ thin films deposited on ITO glass substrates. Applied Surface Science, 2011, 257, 9103-9109.	3.1	34
53	Annealing temperature effect on the properties of mercury-doped TiO ₂ films prepared by sol-gel dip-coating technique. Applied Surface Science, 2011, 257, 5529-5534.	3.1	14
54	Optical properties of GaAs _{0.9-x} N _x Sb _{0.1} alloy films studied by spectroscopic ellipsometry. Thin Solid Films, 2011, 519, 2838-2842.	0.8	4

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55	Photoluminescence studies of 2DEG confinement in InAs ultrathin layer introduced in GaAs/AlGaAs structure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 2134-2138.	1.3	14
56	Analyzing ab initio infrared spectra and electronic properties of polyethylenimine water complexes in the solid state. <i>Computational and Theoretical Chemistry</i> , 2010, 945, 27-32.	1.5	11
57	Correlation between microstructure and optical properties of nano-crystalline TiO ₂ thin films prepared by sol-gel dip coating. <i>Applied Surface Science</i> , 2010, 257, 670-676.	3.1	105
58	Effect of nitrogen on the GaAs _{0.9} xN _x Sb _{0.1} dielectric function from the near-infrared to the ultraviolet. <i>Applied Physics Letters</i> , 2010, 97, 201903.	1.5	17
59	Spectroscopic ellipsometry study of GaAs _{1-x} Bi _x material grown on GaAs substrate by atmospheric pressure metal-organic vapor-phase epitaxy. <i>Applied Physics Letters</i> , 2009, 95, 011910.	1.5	14
60	Optical constants and critical-point parameters of GaAs _{1-x} Sb _x alloy films grown on GaAs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 833-836.	0.8	2
61	Spectroscopic ellipsometry analysis of GaAs _{1-x} N _x layers grown by molecular beam epitaxy. <i>Materials Science and Engineering C</i> , 2008, 28, 640-644.	3.8	9
62	Abnormal optical behaviour of InAsSb quantum dots grown on GaAs substrate by molecular beam epitaxy. <i>Materials Science and Engineering C</i> , 2008, 28, 918-922.	3.8	0
63	Observation of many-body Coulomb interaction effects on the photoluminescence spectra of InAs/GaAs quantum dots. <i>Applied Surface Science</i> , 2008, 254, 3125-3129.	3.1	9
64	Optical properties of GaInNAsSb/GaAs/GaAs _{1-x} N _x (x% ^ˆ 10%) saturable absorber quantum wells. <i>Applied Surface Science</i> , 2008, 254, 7122-7126.	3.1	1
65	Ellipsometric investigation of porous silicon layers for the design of a DBR. <i>EPJ Applied Physics</i> , 2008, 43, 87-91.	0.3	4
66	Strain effects of InP/Si and InP/porous Si studied by spectroscopic ellipsometry. <i>EPJ Applied Physics</i> , 2008, 42, 99-102.	0.3	0
67	Photoluminescence study of the GaAs barrier effect on GaAs/GaInAs/GaAs quantum wells. , 2007, , .		0
68	Optical Constants of As-grown and RTA GaAs _{1-x} N _x Layers Analysed by Spectroscopic Ellipsometry. , 2007, , .		0
69	Redistribution of nitrogen localized states in GaAsN layer doped Silicon. <i>EPJ Applied Physics</i> , 2007, 38, 221-225.	0.3	0
70	Deep Defects Annihilation in GaAs _{1-x} N _x Layers by Si-doping. <i>American Journal of Applied Sciences</i> , 2007, 4, 19-22.	0.1	6